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GaAs InGaP HBT MMIC DRIVER AMPLIFIER, 3.0 - 4.5 GHz

Typical Applications

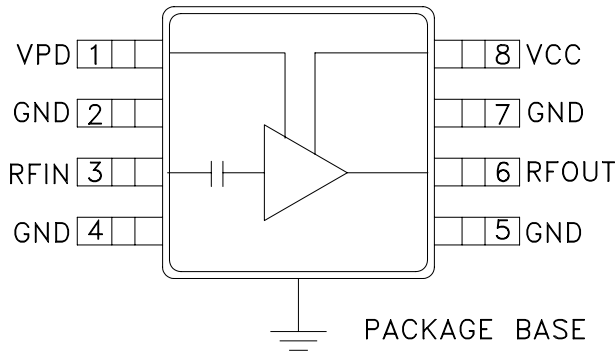
The HMC326MS8G / HMC326MS8GE is ideal for:

- Microwave Radios
- Broadband Radio Systems
- Wireless Local Loop Driver Amplifier

Features

- Psat Output Power: +26 dBm
- > 40% PAE
- Output IP3: +36 dBm
- High Gain: 21 dB
- Vs: +5V
- Ultra Small Package: MSOP8G

Functional Diagram

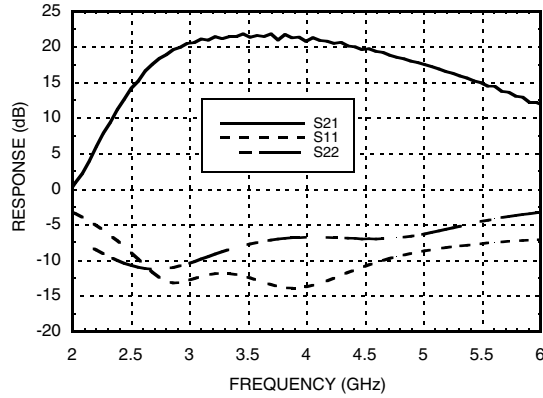
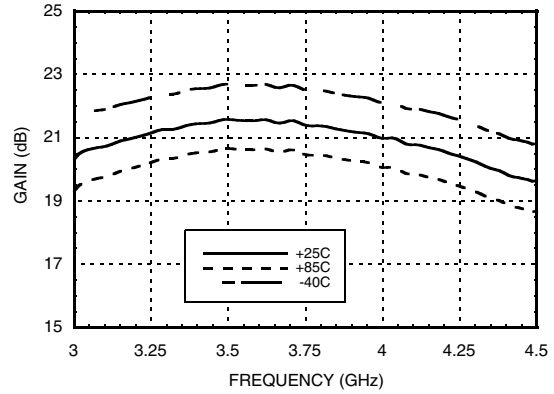
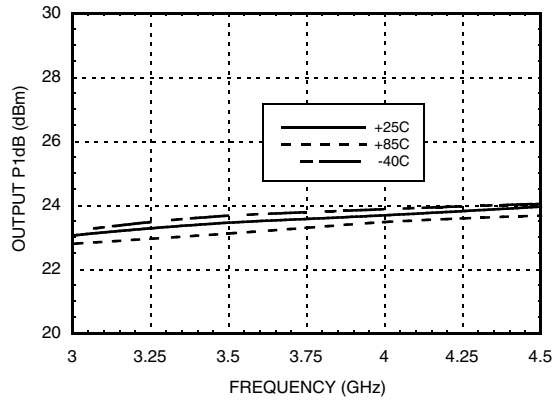
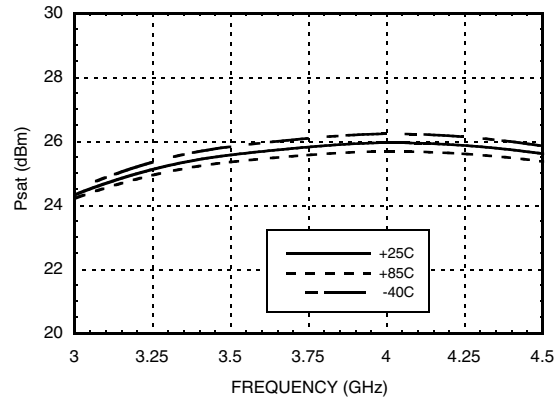
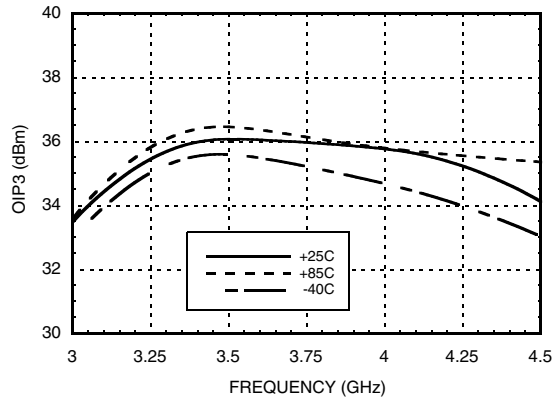
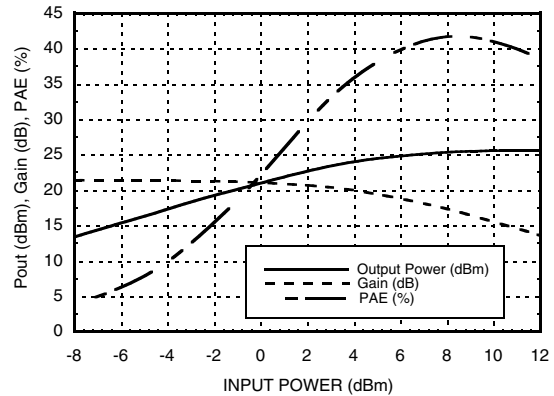


General Description

The HMC326MS8G & HMC326MS8GE are high efficiency GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC driver amplifiers which operate between 3.0 and 4.5 GHz. The amplifier is packaged in a low cost, surface mount 8 leaded package with an exposed base for improved RF and thermal performance. The amplifier provides 21 dB of gain and +26 dBm of saturated power from a +5V supply voltage. Power down capability is available to conserve current consumption when the amplifier is not in use. Internal circuit matching was optimized to provide greater than 40% PAE.

Electrical Specifications, $T_A = +25^\circ C$, $V_s = 5V$, $V_{pd} = 5V$

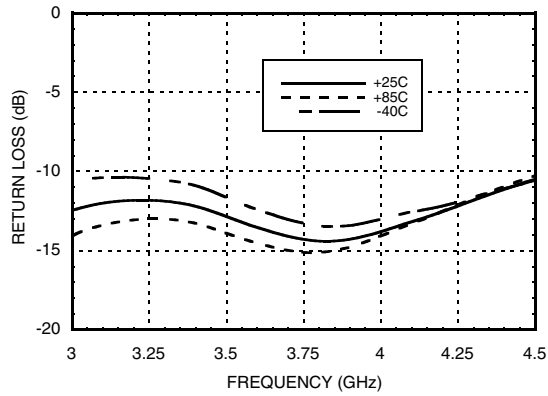
| Parameter | Min. | Typ. | Max. | Units | |
|---|-----------|-------|-------|---------|----|
| Frequency Range | 3.0 - 4.5 | | | GHz | |
| Gain | 18 | 21 | | dB | |
| Gain Variation Over Temperature | | 0.025 | 0.035 | dB / °C | |
| Input Return Loss | | 12 | | dB | |
| Output Return Loss | | 7 | | dB | |
| Output Power for 1dB Compression (P1dB) | 21 | 23.5 | | dBm | |
| Saturated Output Power (Psat) | | 26 | | dBm | |
| Output Third Order Intercept (IP3) | 32 | 36 | | dBm | |
| Noise Figure | | 5 | | dB | |
| Supply Current (Icc) | Vpd = 0V | 1 | | uA | |
| Supply Current (Icc) | Vpd = 5V | 110 | 130 | 160 | mA |
| Control Current (Ipd) | | 7 | | mA | |
| Switching Speed | tOn/tOff | 10 | | ns | |


Broadband Gain & Return Loss

Gain vs. Temperature

P1dB vs. Temperature

Psat vs. Temperature

Output IP3 vs. Temperature

Power Compression @ 3.5 GHz


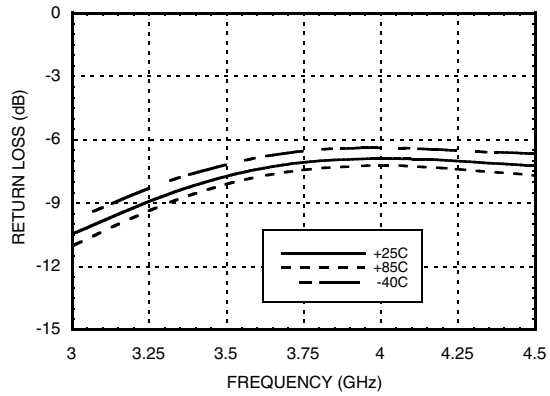


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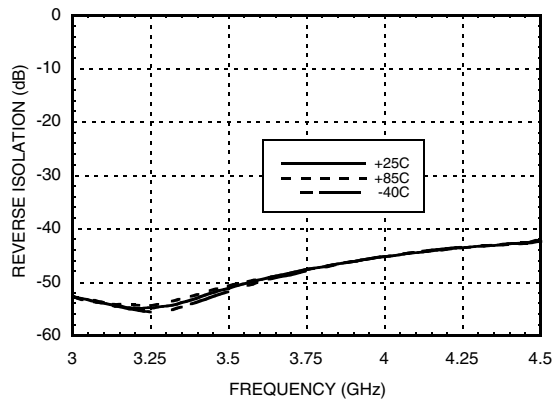
Input Return Loss vs. Temperature



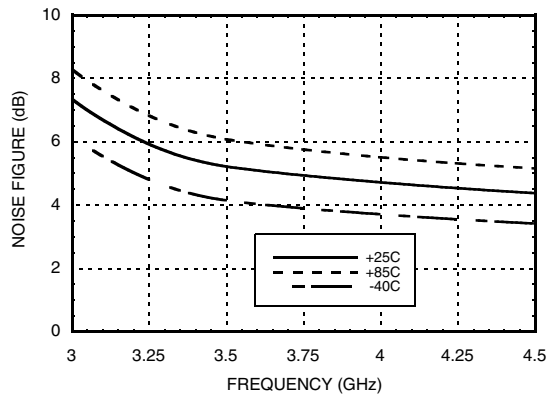
Output Return Loss vs. Temperature



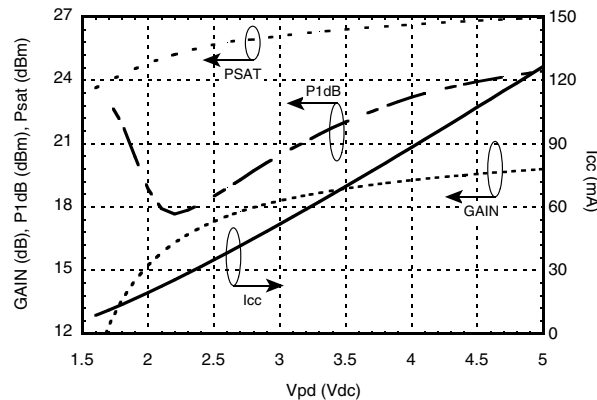
Reverse Isolation vs. Temperature



Noise Figure vs. Temperature



**Gain, Power & Quiescent Supply
Current vs. Vpd @3.5 GHz**



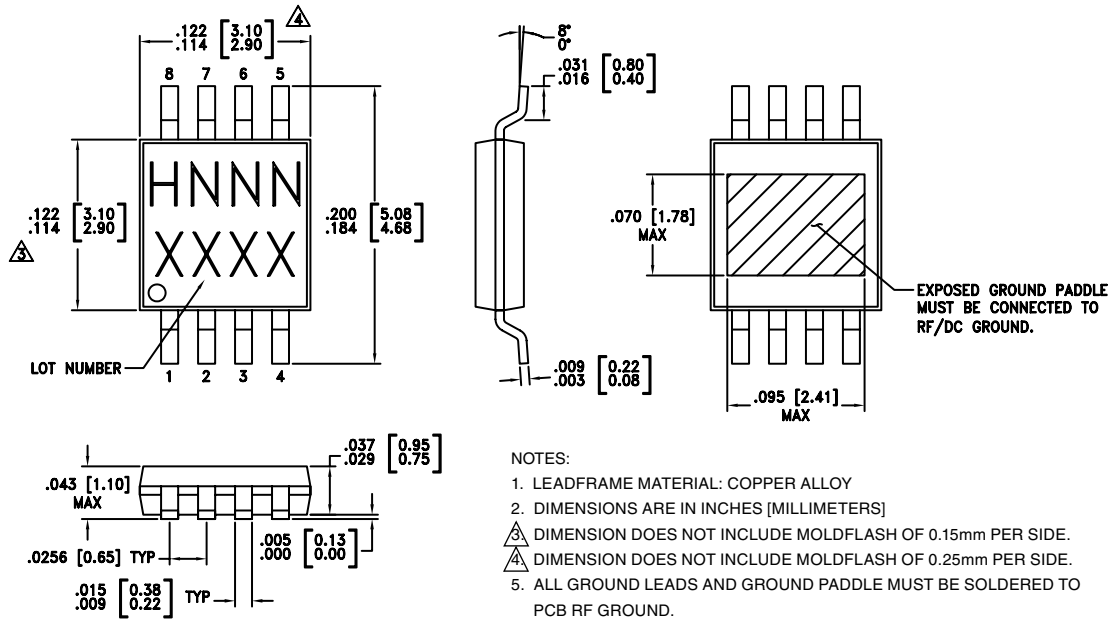
Absolute Maximum Ratings

| | |
|---|----------------|
| Collector Bias Voltage (Vcc) | +5.5 Vdc |
| Control Voltage Range (Vpd) | +5.5 Vdc |
| RF Input Power (RFIN)(Vs = Vpd = +5Vdc) | +15 dBm |
| Junction Temperature | 150 °C |
| Continuous P _{diss} (T = 85 °C) (derate 14 mW/°C above 85 °C) | 0.916 W |
| Thermal Resistance (junction to ground paddle) | 71 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |
| ESD Sensitivity (HBM) | Class 1A |



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



Package Information

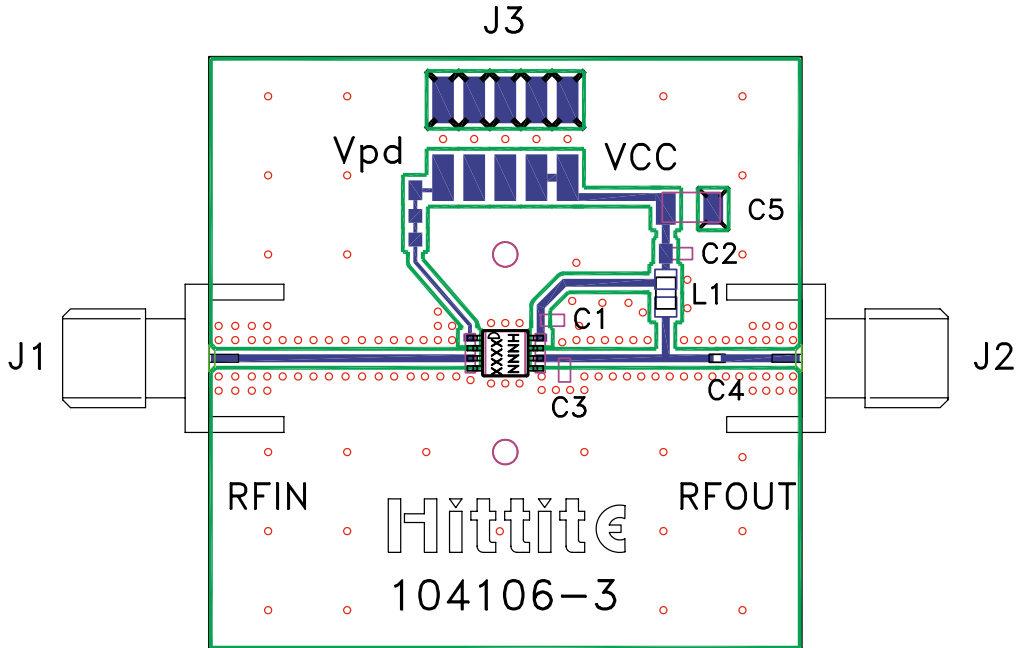
| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[3] |
|-------------|--|---------------|---------------------|--------------------------------|
| HMC326MS8G | Low Stress Injection Molded Plastic | Sn/Pb Solder | MSL1 ^[1] | H326 XXXX |
| HMC326MS8GE | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 ^[2] | H326 XXXX |

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

Evaluation PCB



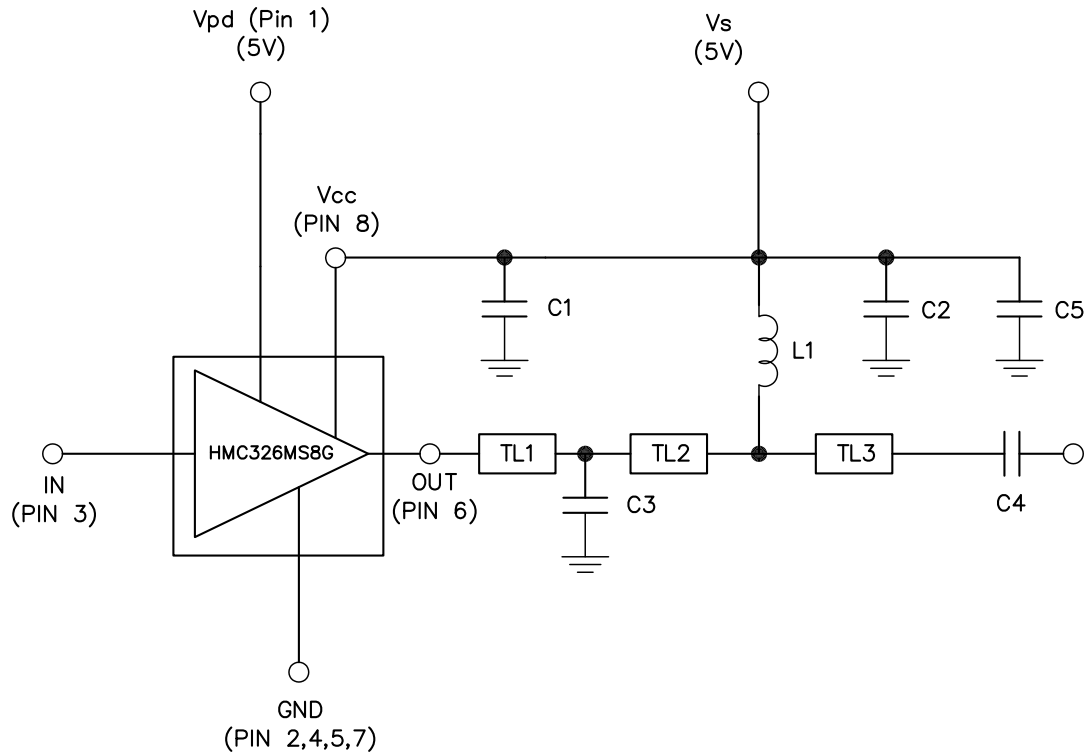
List of Materials for Evaluation PCB 104356 [1]

| Item | Description |
|---------|------------------------------------|
| J1 - J2 | PCB Mount SMA RF Connector |
| J3 | 2mm DC Header |
| C1 - C2 | 330 pF Capacitor, 0603 Pkg. |
| C3 | 0.7 pF Capacitor, 0603 Pkg. |
| C4 | 3.0 pF Capacitor, 0402 Pkg. |
| C5 | 2.2 μF Capacitor, Tantalum |
| L1 | 3.3 nH Inductor, 0805 Pkg. |
| U1 | HMC326MS8G / HMC326MS8GE Amplifier |
| PCB [2] | 104106 Eval Board |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350, 10 mil thick, $\tau_r = 3.48$

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

Application Circuit


| | TL1 | TL2 | TL3 |
|------------------------------|--|---|--|
| Impedance | 50 ohm | 50 ohm | 50 ohm |
| Physical Length | 0.0614" | 0.2561" | 0.110" |
| Electrical Length @ 3.75 GHz | 10.7° | 44.6° | 19.2° |
| Measurement | Center of package pin to center of capacitor C3. | Center of capacitor C3 to center TL for inductor. | Center of TL for inductor to edge of capacitor C4. |

PCB Material: 10 mil Rogers 4350 or Arlon 25FR

| Recommended Component Values | |
|------------------------------|-------------|
| L1 | 3.3 nH |
| C1 - C2 | 330 pF |
| C3 | 0.7 pF |
| C4 | 3.0 pF |
| C5 | 2.2 μ F |